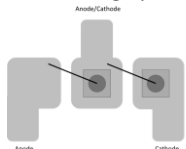
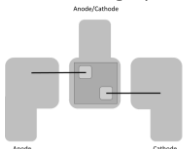




Title of Change:	Qualifying a new die design for BAV99LT1G and BAV99LT3G Switching Diode in SOT23 package.	
Proposed first ship date:	23 June 2018 or earlier after customer approval	
Contact information:	Contact your local ON Semiconductor Sales Office or <farrah.omar@onsemi.com>	
Samples:	Contact your local ON Semiconductor Sales Office	
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or <Dustin.Tenney@onsemi.com>	
Type of notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact <PCN.Support@onsemi.com>.	
Change Part Identification:	Customer may receive the affected parts from month of May 2018 onwards once FPCN expire.	
Change category:	<input type="checkbox"/> Wafer Fab Change <input type="checkbox"/> Assembly Change <input type="checkbox"/> Test Change <input checked="" type="checkbox"/> Other <u>New Die Design</u>	
Change Sub-Category(s):	<input checked="" type="checkbox"/> Manufacturing Site Change/Addition <input type="checkbox"/> Material Change <input type="checkbox"/> Datasheet/Product Doc change <input type="checkbox"/> Manufacturing Process Change <input type="checkbox"/> Product specific change <input type="checkbox"/> Shipping/Packaging/Marking <input type="checkbox"/> Other: _____	
Sites Affected:	ON Semiconductor Sites: ON ISMF, Malaysia ON Niigata, Japan	External Foundry/Subcon Sites: None
Description and Purpose: ON Semiconductor is notifying customers of its plan to qualify a new die design for BAV99LT1G and BAV99LT3G Switching Diode in SOT23 package. This new die design will be sourced from Niigata Fab (Japan). Old design will continue to be sourced from Malaysia Fab(current location)		
<div style="display: flex; justify-content: space-around; align-items: flex-start;"> <div style="text-align: center;"> <p><u>Old die design picture:</u></p>  </div> <div style="text-align: center;"> <p><u>New die design picture:</u></p>  </div> </div> <p>The Niigata Fab facility is an ON Semiconductor owned Wafer Fab that has been producing products for ON Semiconductor. Several existing technologies within ON Semiconductor's product families are currently sourced from Niigata Fab. ON Semiconductor Niigata Wafer Fab is an internal factory that is TS16949, ISO-9001 and ISO-14000 certified.</p> <p>Qualification tests are designed to show that the reliability of the impacted devices will continue to meet or exceed ON Semiconductor standards.</p>		

**Reliability Data Summary:****QV DEVICE NAME:** BAV99LT1G**PACKAGE:** SOT-23

Test	Specification	Condition	Interval	Results
HTRB	JESD22-A108	Ta=150 °C, 100% max rated V	1008 hrs	0/240
HTSL	JESD22-A103	Ta= 150 °C	2016 hrs	0/240
IOL	MIL-STD-750 (M1037) AEC-Q101	Ta=+25°C, delta Tj=100°C On/off = 2 min	7500 cyc	0/240
TC	JESD22-A104	Ta= -65°C to +150°C	1000 cyc	0/240
H3TRB	JESD22-A110	85°C, 85% RH, 18.8psig, bias	2016 hrs	0/240
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig, unbiased	96 hrs	0/240
PC	J-STD-020 JESD-A113	MSL 1 @ 260 °C		
RSH	JESD22- B106	Ta = 265C, 10 sec		0/90
SD	JSTD002	Ta = 245C, 10 sec		0/50

Electrical Characteristic Summary:

The temperature characterization and ESD performance meet datasheet specification. Detail of electrical characterization result is available upon request.

List of Affected Standard Parts:

Part Number	Qualification Vehicle
BAV99LT1G	BAV99LT1G
BAV99LT3G	